

# ST2310FX

# HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

- n NEW SERIES, ENHANCED PERFORMANCE
- n FULLY INSULATED PACKAGE (U.L. COMPLIANT) FOR EASY MOUNTING
- n HIGH VOLTAGE CAPABILITY (1500 V)
- n HIGH SWITCHING SPEED
- n TIGTHER h<sub>fe</sub> CONTROL
- n IMPROVED RUGGEDNESS

#### APPLICATION

HORIZONTAL DEFLECTION FOR MONITORS 17 " AND HIGH END TVs

#### DESCRIPTION

The device is manufactured using Diffused Collector technology for more stable operation Vs base drive circuit variations resulting in very low worst case dissipation.



#### Figure 2: Internal Schematic Diagram



#### Table 1: Order Code

Part Number	Marking	Package	Packaging
ST2310FX	2310FX	ISOWATT218FX	TUBE

Symbol	Parameter	Value	Unit
V <sub>CES</sub>	Collector-Emitter Voltage (V <sub>BE</sub> = 0)	1500	V
V <sub>CEO</sub>	Collector-Emitter Voltage (I <sub>B</sub> = 0)	600	V
V <sub>EBO</sub>	Emitter-Base Voltage (I <sub>C</sub> = 0)	7	V
۱ <sub>C</sub>	Collector Current	12	A
I <sub>CM</sub>	Collector Peak Current (t <sub>p</sub> < 5ms)	25	А
Ι <sub>Β</sub>	Base Current	7	Α
P <sub>tot</sub>	Total Dissipation at $T_{C}$ = 25 °C	65	W
V <sub>isol</sub>	Insulation Withstand Voltage (RMS) from All Three Leads to External Heatsink	2500	V
T <sub>stg</sub>	Storage Temperature	-65 to 150	°C
TJ	Max. Operating Junction Temperature	150	°C

#### **Table 2: Absolute Maximum Ratings**

### Table 3: Thermal Data

Symbol	Parameter		Unit
R <sub>thj-case</sub>	Thermal Resistance Junction-Case Max	1.9	°C/W

# Table 4: Electrical Characteristics ( $T_{case}$ = 25 °C unless otherwise specified)

Symbol	Parameter	Test Co	onditions	Min.	Тур.	Max.	Unit
I <sub>CES</sub>	Collector Cut-off Current	V <sub>CE</sub> = 1500 V				1	mA
	(V <sub>BE</sub> = 0)	V <sub>CE</sub> = 1500 V	T <sub>j</sub> = 125 <sup>o</sup> C			2	mA
I <sub>EBO</sub>	Emitter Cut-off Current	V <sub>EB</sub> = 7 V				1	mA
	$(I_{\rm C}=0)$						
V <sub>CE(sus)</sub> *	Collector-Emitter	I <sub>C</sub> = 100 mA	L = 25 mH	600			V
	Sustaining Voltage						
	(I <sub>B</sub> = 0)						
V <sub>CE(sat)</sub> *	Collector-Emitter	I <sub>C</sub> = 7 A	I <sub>B</sub> = 1.75 A			3	V
	Saturation Voltage						
V <sub>BE(sat)</sub> *	Base-Emitter	I <sub>C</sub> = 7 A	I <sub>B</sub> = 1.75 A			1.1	V
	Saturation Voltage						
h <sub>FE</sub> *	DC Current Gain	I <sub>C</sub> = 1 A	V <sub>CE</sub> = 5 V		25		
		I <sub>C</sub> = 7 A	V <sub>CE</sub> = 1 V		5.5		
		I <sub>C</sub> = 7 A	$V_{CE}$ = 5 V	6.5		9.5	
	INDUCTIVE LOAD	I <sub>C</sub> = 6 A	f <sub>h</sub> = 64 KHz				
t <sub>s</sub>	Storage Time	$I_{B(on)} = 1 A$	V <sub>BE(off)</sub> = -2.5 V		2.3	3	μs
t <sub>f</sub>	Fall Time	L <sub>BB(off)</sub> = 1.3 μH	(see figure 14)		0.16	0.35	μs

\* Pulsed: Pulsed duration = 300  $\mu$ s, duty cycle  $\leq$  1.5 %.

Figure 3: Safe Operating Area



Figure 4: Derating Curve



Figure 5: Collector-Emitter Saturation Voltage



Figure 6: Thermal Impedance



Figure 7: Output Chatacterisctics



Figure 8: Base-Emitter Saturation Voltage



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Figure 9: DC Current Gain



Figure 10: Power Losses



Figure 11: Reverse Biased Safe Operating Area



Figure 12: DC Current Gain



Figure 13: Switching Time Inductive Load









# **ISOWATT218FX MECHANICAL DATA**

DIM.	mm.				
	MIN.	ТҮР	MAX.		
A	5.30		5.70		
С	2.80		3.20		
D	3.10		3.50		
D1	1.80		2.20		
E	0.80		1.10		
F	0.65		0.95		
F2	1.80		2.20		
G	10.30		11.50		
G1		5.45			
Н	15.30		15.70		
L	9		10.20		
L2	22.80		23.20		
L3	26.30		26.70		
L4	43.20		44.40		
L5	4.30		4.70		
L6	24.30		24.70		
L7	14.60		15		
N	1.80		2.20		
R	3.80		4.20		
Dia	3.40		3.80		



## Table 5: Revision History

Date	Release	Change Designator
01-Jul-2004	1	First Release.
08-Feb-2005	2	Table 1 has been added on page 1.



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